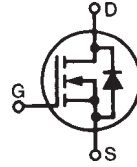


**Polar™ HiPerFET™
Power MOSFET**

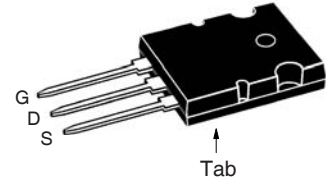
**IXFK250N10P
IXFX250N10P**

V_{DSS} = 100V
I_{D25} = 250A
R_{DS(on)} ≤ 6.5mΩ
t_{rr} ≤ 200ns

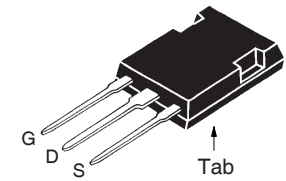
N-Channel Enhancement Mode
 Avalanche Rated
 Fast Intrinsic Diode



TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate D = Drain
 S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 175°C	100	V
V _{DGR}	T _J = 25°C to 175°C, R _{GS} = 1MΩ	100	V
V _{GSS}	Continuous	± 20	V
V _{GSM}	Transient	± 30	V
I _{D25}	T _C = 25°C (Chip Capability)	250	A
I _{LRMS}	Lead Current Limit, RMS	160	A
I _{DM}	T _C = 25°C, Pulse Width Limited by T _{JM}	700	A
I _A	T _C = 25°C	125	A
E _{AS}	T _C = 25°C	3	J
P _D	T _C = 25°C	1250	W
dv/dt	I _S ≤ I _{DM} , V _{DD} ≤ V _{DSS} , T _J ≤ 175°C	20	V/ns
T _J		-55 ... +175	°C
T _{JM}		175	°C
T _{stg}		-55 ... +175	°C
T _L	1.6mm (0.062 in.) from Case for 10s	300	°C
T _{SOLD}	Plastic Body for 10s	260	°C
M _d	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
F _C	Mounting Force (PLUS247)	20..120 /4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

Symbol	Test Conditions (T _J = 25°C Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV _{DSS}	V _{GS} = 0V, I _D = 3mA	100		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 1mA	3.0		5.0 V
I _{GSS}	V _{GS} = ± 20V, V _{DS} = 0V			± 200 nA
I _{DSS}	V _{DS} = V _{DSS} , V _{GS} = 0V T _J = 150°C			50 μA 1 mA
R _{DS(on)}	V _{GS} = 10V, I _D = 50A, Note 1			6.5 mΩ

Features

- Dynamic dv/dt Rating
- Avalanche Rated
- Fast Intrinsic Diode
- Low Q_G and R_{DS(on)}
- Low Package Inductance

Advantages

- Easy to Mount
- Space Savings

Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- Uninterrupted Power Supplies
- AC Motor Drives
- High Speed Power Switching Applications

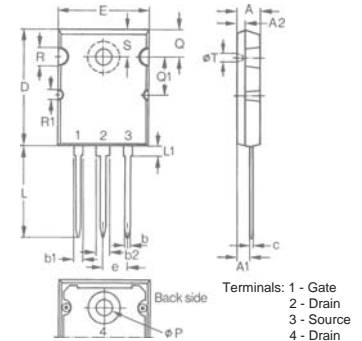
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}, I_D = 60\text{A}$, Note 1	50	83	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		16	nF
C_{oss}			4470	pF
C_{rss}			290	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		25	ns
t_r			30	ns
$t_{d(off)}$			50	ns
t_f			18	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		205	nC
Q_{gs}			77	nC
Q_{gd}			80	nC
R_{thJC}			0.12	$^\circ\text{C/W}$
R_{thCS}		0.15		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			250 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			750 A
V_{SD}	$I_F = 100\text{A}, V_{GS} = 0\text{V}$, Note 1			1.3 V
t_{rr}	$I_F = 125\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 50\text{V}, V_{GS} = 0\text{V}$			200 ns
Q_{RM}			0.7	μC
I_{RM}			10.4	A

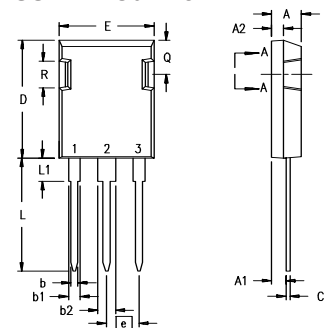
Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

TO-264 Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

PLUS247™ Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

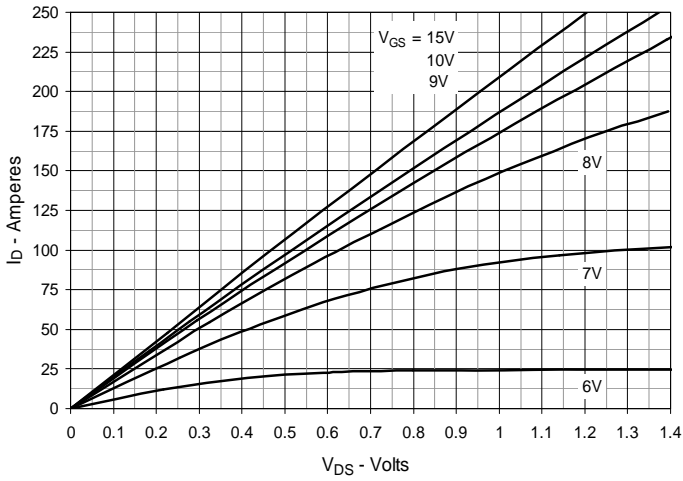


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

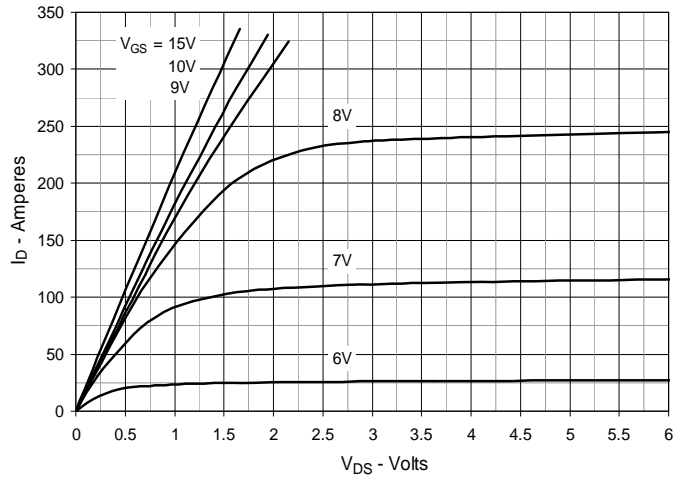


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

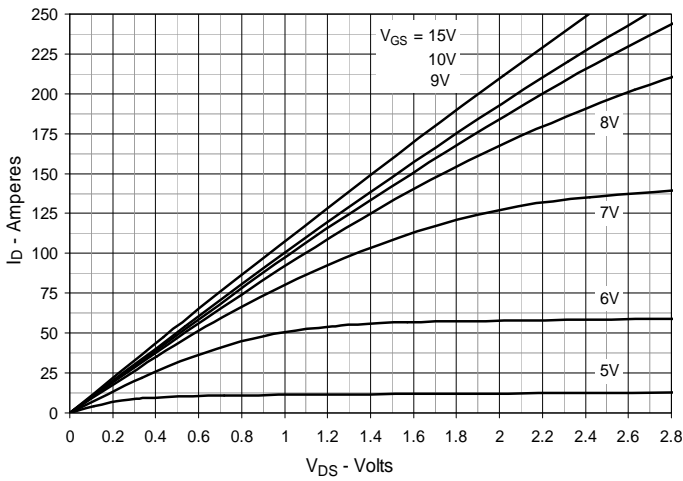


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 125\text{A}$ Value vs. Junction Temperature

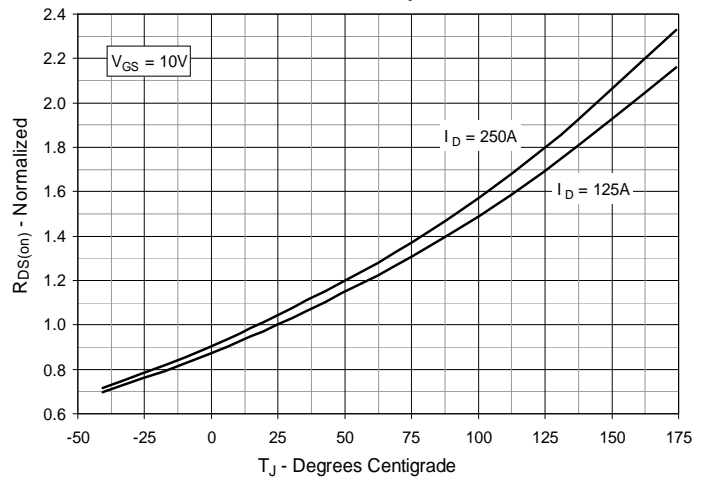


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 125\text{A}$ Value vs. Drain Current

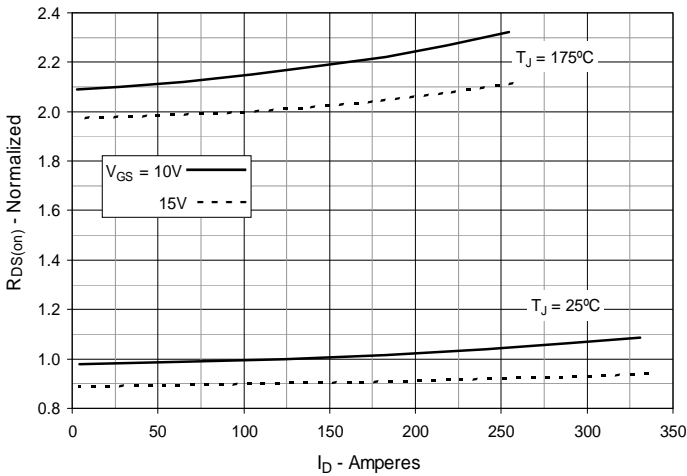


Fig. 6. Maximum Drain Current vs. Case Temperature

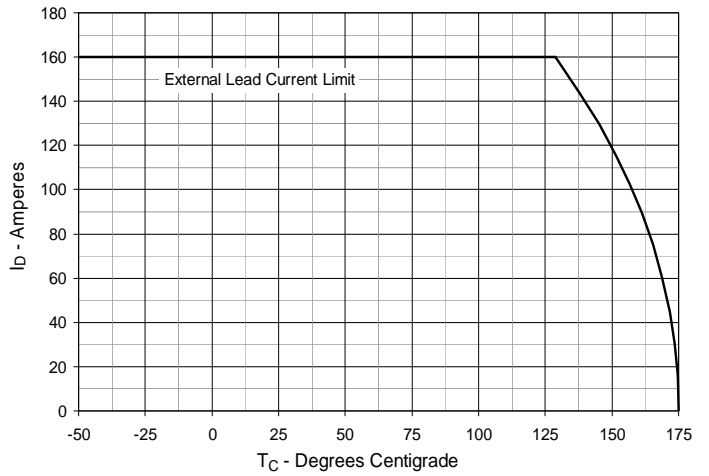


Fig. 7. Input Admittance

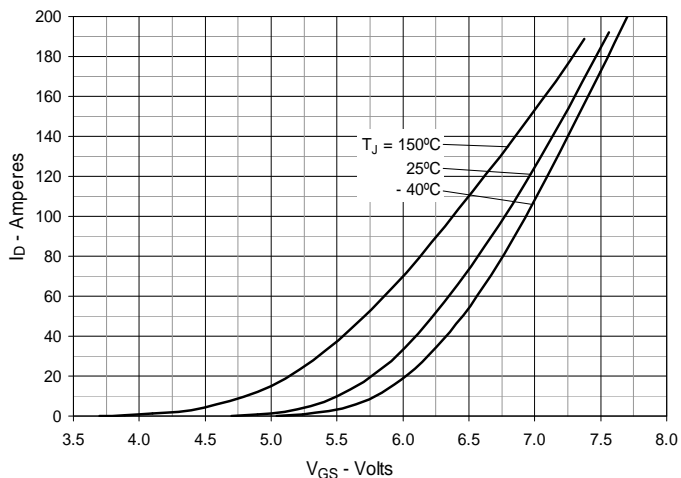


Fig. 8. Transconductance

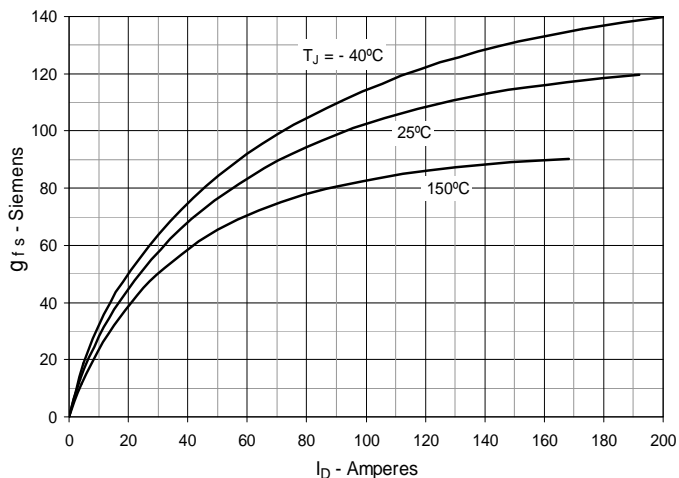


Fig. 9. Forward Voltage Drop of Intrinsic Diode

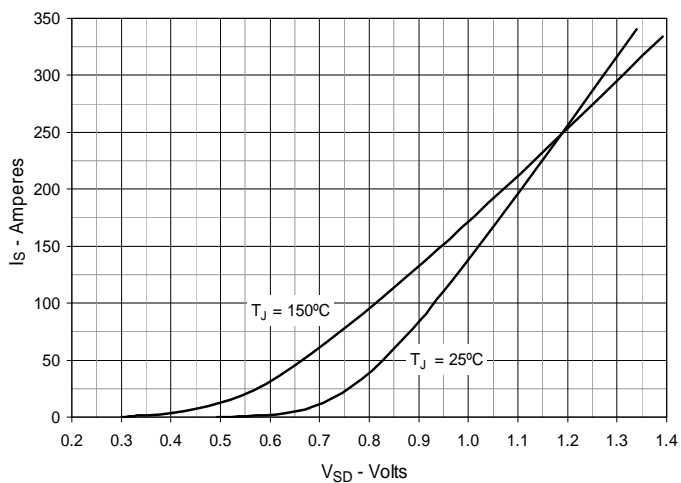


Fig. 10. Gate Charge

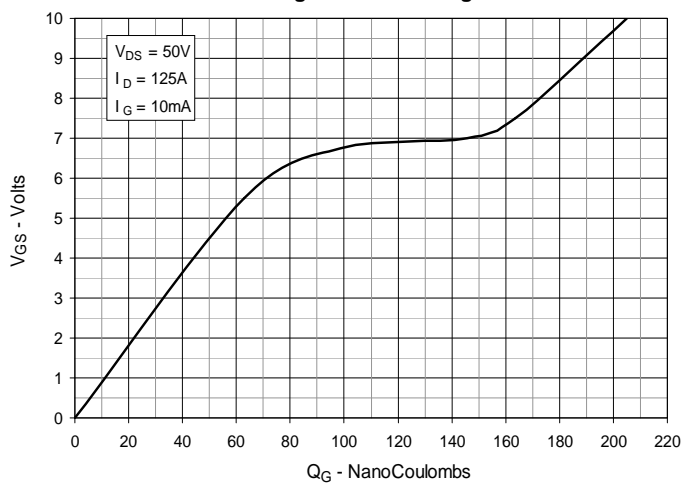


Fig. 11. Capacitance

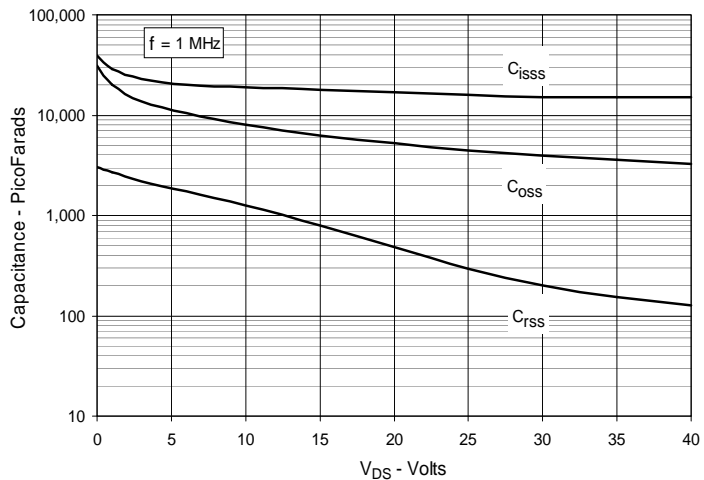


Fig. 12. Forward-Bias Safe Operating Area

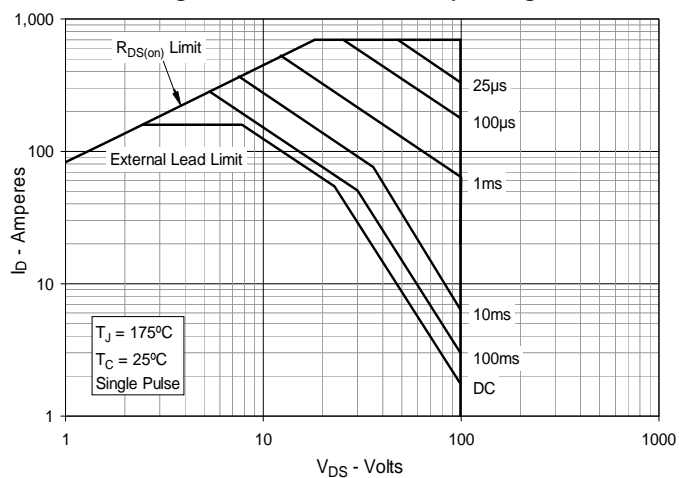


Fig. 13. Maximum Transient Thermal Impedance

